

12-36GHz Frequency Multiplier

GaAs Monolithic Microwave IC

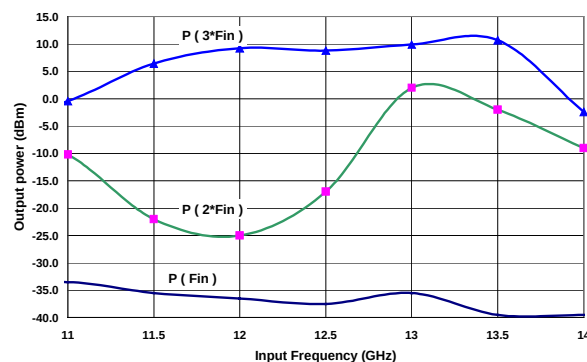
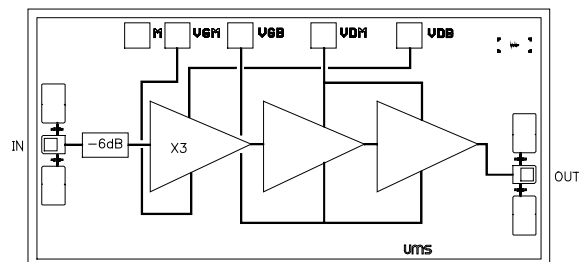
Description

The CHX1094 is a cascaded frequency multiplier by 3 monolithic circuit. It is designed for a wide range of applications, from military to commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a P-HEMT process, 0.25 μ m gate length, via holes through the substrate, air bridges and electron beam gate lithography.

Main Features

- Broadband performances : 12-13.5GHz
- 10dBm output power for +14dBm input power
- DC bias : Vd=3.Volt @Id=60mA
- Chip size : 2.07 x 1.03 x 0.10 mm



typical measurement

Main Characteristics

Tamb. = 25°C

Symbol	Parameter	Min	Typ	Max	Unit
Fin	Input frequency range	12		13.5	GHz
Fout	Output frequency range	36		40.5	GHz
Pin	Input power		14		dBm
Pout	Output power @ Pin= 14dBm		10		dBm

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Electrical Characteristics

Tamb = +25°C, Vgm = -1.5V , Vgb = -0.2V.

Symbol	Parameter	Min	Typ	Max	Typ	Unit
Fin	Input frequency range	12		13.5	14	GHz
Fout	Output frequency range	36		40.5	42	GHz
Pin	Input power	12	14	16	16	dBm
Pout	Output power @ Pin=14dBm	8	10		5	dBm
H3/H2	2 nd Harmonic rejection (Pin ≤ 14dBm)	8	10		5	dBc
H3/H1	Fund. rejection (Pin ≤ 14dBm)	30			35	dBc
VSWRin	Input VSWR			2:1	2:1	
VSWRout	Output VSWR			2.5:1	2.5:1	
Vd	DC voltage	2.5		3.5	4	V
Id	Bias current		60	80	80	mA

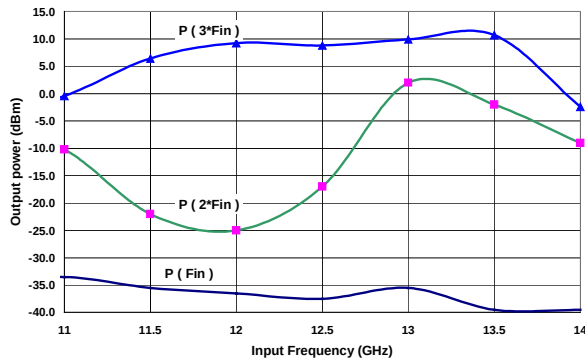
Absolute Maximum Ratings

Tamb. = 25°C (1)

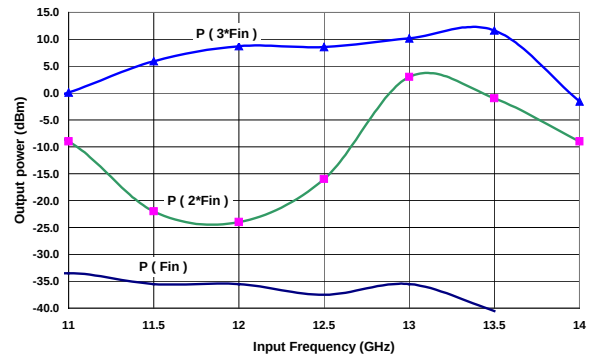
Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	4.5	V
Id	Drain bias current	120	mA
Vg	Gate bias voltage	-2 to +0.4	V
Ta	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +155	°C

(1) Operation above anyone of these parameters may cause permanent damage of this device.

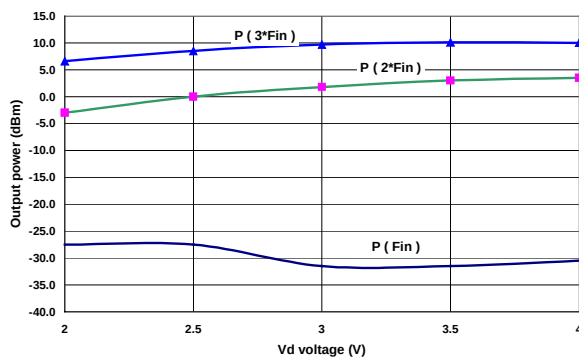
Typical on Jig Measurements.



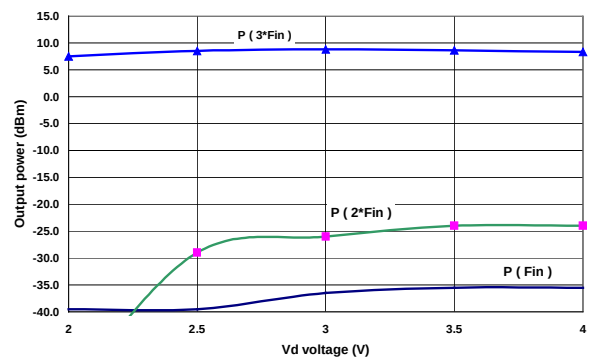
Pout versus Fin @ Pin=14 dBm & Vd=3V



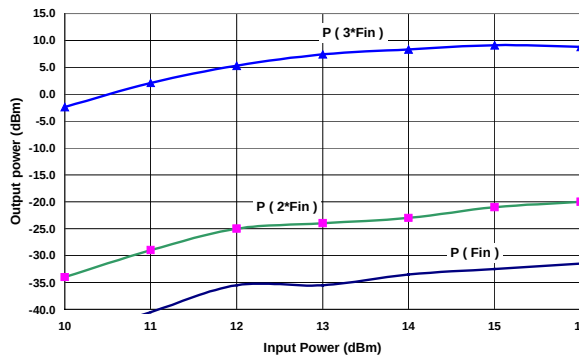
Pout versus Fin @ Pin=14 dBm & Vd=3.5V



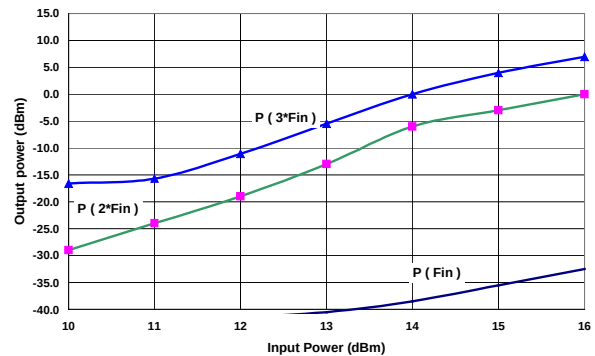
Pout versus Vd @ Pin=14dBm & Fin=13GHz



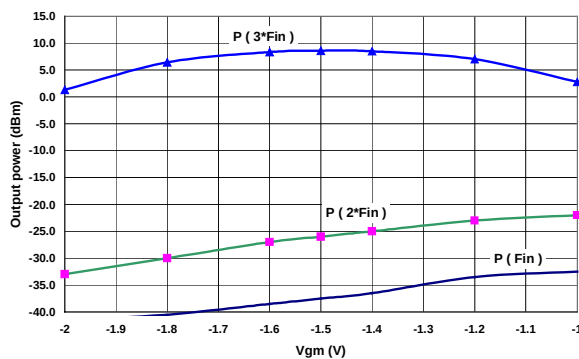
Pout versus Vd @ Pin=14dBm & Fin=12GHz



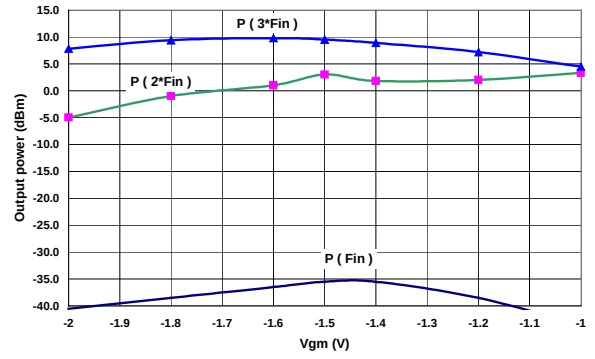
Pout versus Pin @ Fin=12GHz & Vd=3V



Pout versus Pin @ Fin=14GHz & Vd=4V

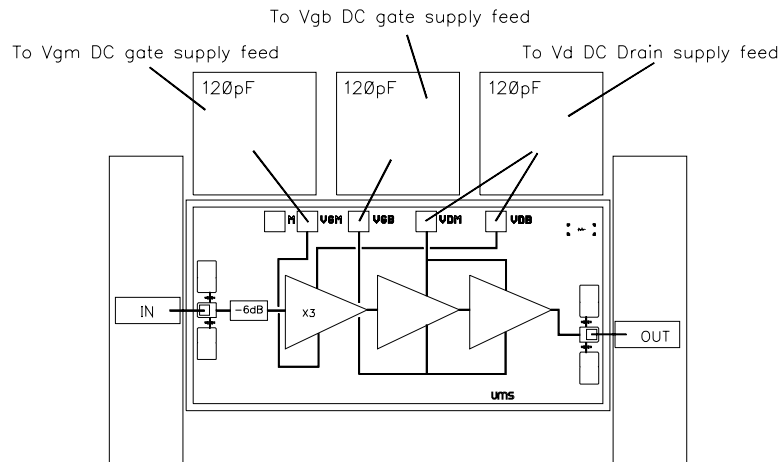


Pout versus Vgm @ Fin=12GHz & Vd=3V

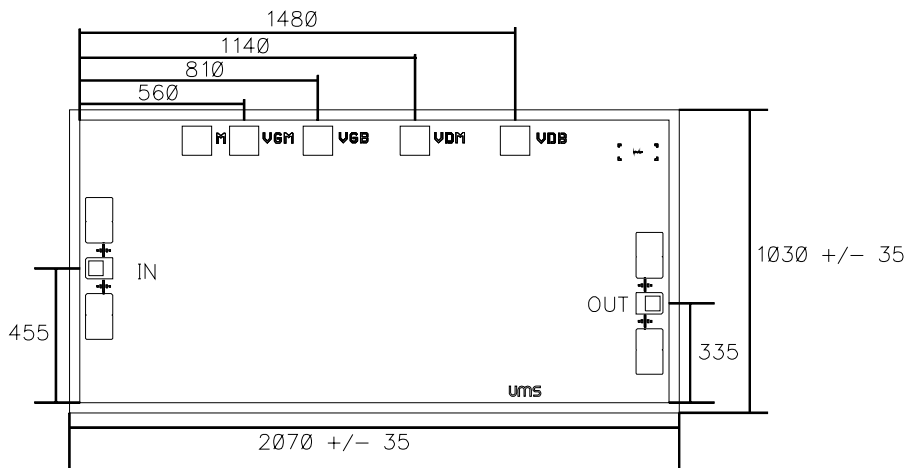


Pout versus Vgm @ Fin=13GHz & Vd=3V

Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25 μ m diameter gold wire is to be preferred
Bond Pad:100 x 100 μ m².



Bonding pad positions.

(Chip thickness : 100 μ m. All dimensions are in micrometers)

Ordering Information

Chip form : CHX1094-99F/00

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